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Attorney's Docket No.: 07977-175002 / US3397

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yamazaki, et/al. Art Unit : 2815  
Serial No.: 09/736,724 Examiner : Paul E. Brock  
Filed : December 13, 2000  
Title : INSULATED GATE SEMICONDUCTOR DEVICE AND METHOD OF  
MANUFACTURING THE SAME

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE

In response to the action mailed August 1, 2001, please  
amend the application as follows:

In the claims:

Please amend claim 1, 3, 5, 7, 9, 11, 13, 15, 17, 18, 19,  
20, 21, 22, 23, and 66 as follows:

1. (Amended) A method of manufacturing an insulated gate  
semiconductor device, said method comprising the steps of:  
forming a resist over a crystal semiconductor  
comprising a part to become a channel forming region;  
forming a dotted hole in said resist by patterning  
said resist using electron drawing method or FIB method;  
forming an intrinsic or substantially intrinsic region  
and an impurity region in said part to become the channel  
forming region by introducing a first impurity into said  
impurity region through said resist having said dotted hole,  
said first impurity being selected from the group consisting of  
carbon, nitrogen and oxygen; and

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